Abstracts

Performance and Limitations of FETs as Microwave Power Amplifiers

L. Napoli and R. DeBrecht. "Performance and Limitations of FETs as Microwave Power Amplifiers." 1973 G-MTT International Microwave Symposium Digest of Technical Papers 73.1 (1973 [MWSYM]): 230-232.

The GaAs FET has excellent potential as a microwave power amplifier and has demonstrated an f/sub t/² (PX) product exceeding that of silicon bipolar devices. The design, fabrication, and performance limitations of GaAs power FETs is discussed. Experimental results for a multigate 4 GHz device and a single gate 7 GHz device are presented.

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